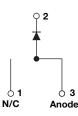
VS-HFA16TB120SHM3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 16 A



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PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	16 A							
V _R	1200 V							
V _F at I _F	3.0 V							
t _{rr} (typ.)	30 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Meets JESD 201 class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TB120SHM3 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120SHM3 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120SHM3 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	16						
Single pulse forward current	I _{FSM}		190	А					
Maximum repetitive forward current	I _{FRM}		64						
Maximum namer discipation	Р	T _C = 25 °C	151	W					
Maximum power dissipation	PD	T _C = 100 °C	60	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

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Document Number: 94991

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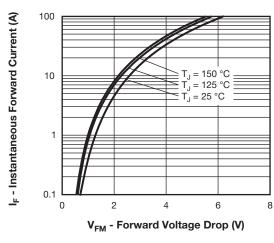
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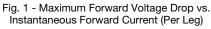
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ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS						
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-			
Maximum forward voltage		I _F = 16 A		-	2.5	3.0	V		
	V _{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93			
		I _F = 16 A, T _J = 125 °C		-	2.3	2.7			
Maximum reverse		$V_{R} = V_{R}$ rated	Coofig 0	-	0.75	20			
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	375	2000	μA		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	27	40	pF		
Series inductance	LS	Measured lead to lead 5 mm from pa	ackage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS				UNITS		
Reverse recovery time See fig. 5 and 10	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-			
	t _{rr1}	T _J = 25 °C		-	90	-	ns A nC		
	t _{rr2}	T _J = 125 °C		-	164	-			
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 16 A$	-	5.8	-			
See fig. 6	I _{RRM2}	T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	8.3	-			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	-			
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	-	nc		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	0.83	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r∨ vv			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking device		Case style D ² PAK		HFA16T	B120SH				





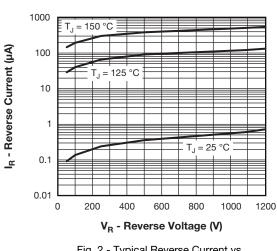


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

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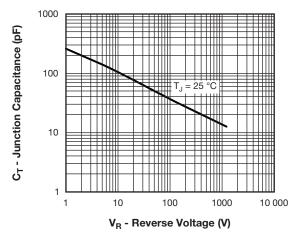


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

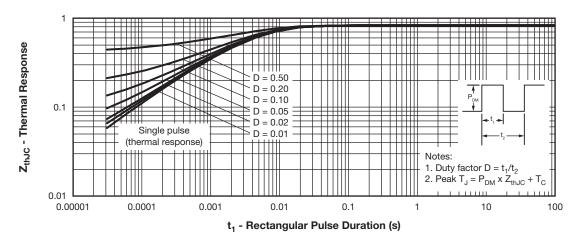


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics (Per Leg)

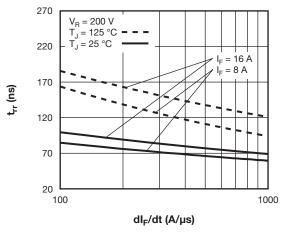


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

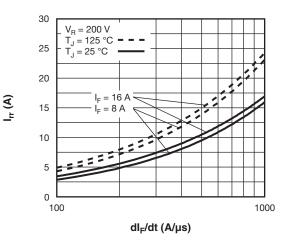


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

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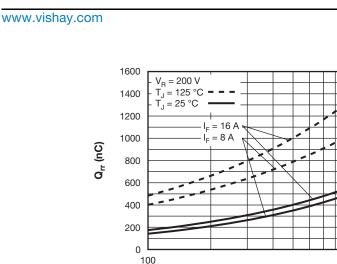
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1000

dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

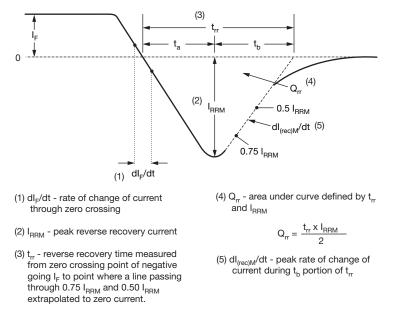


Fig. 8 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	16	тв	120	S	L	Н	М3	
		2	3	4	5	6	7	8	9	10	
	1	- Visł	nay Sem	niconduc	ctors pro	oduct					
	2										
	3	 Process designator: A = Electron irradiated 									
	4	4 - Current rating (16 = 16 A)									
	5	- Pac	kage ou	ıtline (Tl	3 = TO-	220, 2 l	eads)				
	6	- Voli	age rati	ng (120	= 1200	V)					
	7	- S =	D ² PAK								
	8	• N	one = T	ube							
		 L = tape and reel (left oriented) 									
		 R = tape and reel (right oriented) 									
	9.	• H=	AEC-Q	101 qua	lified						
	10 ·	- M3	= halog	en-free,	RoHS-0	complia	nt, and	terminat	tions lea	ad (Pb)-f	

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95046							
Part marking information	www.vishay.com/doc?95444							
Packaging information	www.vishay.com/doc?95032							

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA16TB120SHM3	50	1000	Antistatic plastic tube						
VS-HFA16TB120SRHM3	800	800	13" diameter reel						
VS-HFA16TB120SLHM3	800	800	13" diameter reel						

Outline Dimensions



D²PAK

DIMENSIONS in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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